
FEATURES

- Ø0.05 mm active area
- Low dark current
- Fast response time
- High speed epitaxy

DESCRIPTION

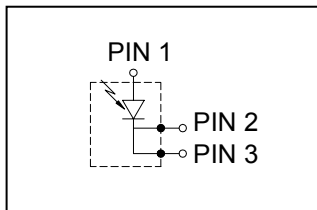
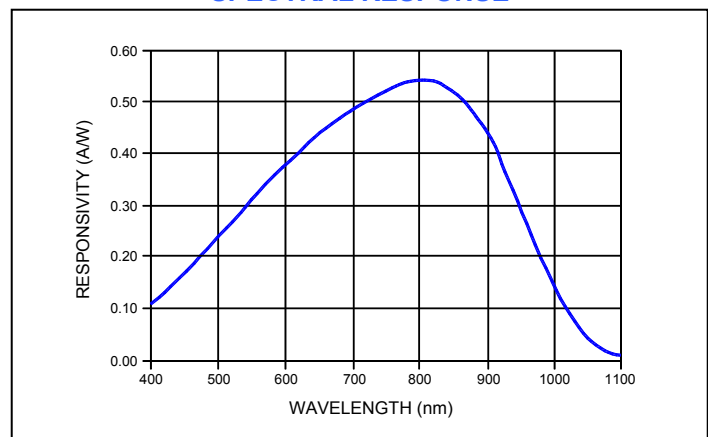
20.0 mm² High Speed Epitaxy Photodiode with P on N construction. Hermetically packaged in a TO-8 with a clear borosilicate glass window cap.

APPLICATIONS

- High speed photometry
- Pulsed light detection
- Fiber optic light monitoring


ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS
T _{STG}	Storage Temp	-55	+125	°C
T _{OP}	Operating Temp	-40	+100	°C
V _{R(OP)}	Reverse Operating Voltage	-	50	V
I _(PEAK)	Peak DC Current	-	10	mA

SCHEMATIC

SPECTRAL RESPONSE

ELECTRO-OPTICAL CHARACTERISTICS @ 22° C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
R _{SH}	Shunt Resistance	V _R = ±10 mV	100	200	---	MΩ
I _D	Dark Current	V _R = 20 V	---	2.0	5.0	nA
C	Capacitance	V _R = 0 V	---	300	---	pF
		V _R = 20 V	---	65	---	
	Responsivity	V _R = 0 V; λ = 632 nm	---	0.40	---	A/W
		V _R = 0 V; λ = 800 nm	---	0.52	---	
NEP	Noise Equivalent Power	V _R = 0 V; λ = 850 nm; R _L = 50 Ω	---	8.0 × 10 ⁻¹⁴	---	W/Hz ^{1/2}
		V _R = 20 V; λ = 850 nm; R _L = 50 Ω	---	1.5 × 10 ⁻¹³	---	
V _{BR}	Breakdown Voltage	I _R = 10 μA	30	50	---	V
t _r	Rise Time	V _R = 20 V; λ = 850 nm; R _L = 50 Ω	---	3.5	---	ns

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.

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